

**AMENDMENTS TO THE SUBSTITUTE SPECIFICATION:**

**Please add the following new paragraph after the paragraph ending on line 2 of page 1:**

**CROSS REFERENCE TO RELATED APPLICATIONS**

This application is a continuation-in-part (CIP) of U.S. Patent Application Serial No. 09/260,074, filed on March 2, 1999, entitled "SEMICONDUCTOR MANUFACTURING METHODS, PLASMA PROCESSING METHODS AND PLASMA PROCESSING APPARATUSES", now issued as U.S. Patent No. 6,355,570, the subject matter of which is incorporated by reference herein.

**Please replace the paragraph beginning at page 13, line 27, with the following rewritten paragraph:**

~~Fig. 28(a) is a front view and Fig. 28(b) is a plane~~28 is a view of a parallel  
electrodes type plasma etching apparatus.

**Please replace the paragraph beginning at page 14, line 2, with the following rewritten paragraph:**

~~Fig. 29(a) is a front view and Fig. 29(b) is a plane~~29 is a view of a parallel  
electrodes type plasma etching apparatus equipped with a device for measuring fine particles suspended in plasma according to the present invention.

**Please replace the paragraph beginning at page 25, line 24, with the following rewritten paragraph:**

~~The for~~The measuring fine particles suspended in a plasma according to this embodiment is set up to be mounted in an etching apparatus that is already equipped with an observation window 11 to allow plasma illumination inspection and

the like. This embodiment provides a device for measuring fine particles suspended in a plasma that is effective for cases where there is no Brewster's angle at the observation window, i.e., where a large amount of light is reflected from the surface of the observation window.